

Low Noise, JFET Input Operational Amplifiers

These low noise JFET input operational amplifiers combine two state—of—the—art analog technologies on a single monolithic integrated circuit. Each internally compensated operational amplifier has well matched high voltage JFET input device for low input offset voltage. The BIFET technology provides wide bandwidths and fast slew rates with low input bias currents, input offset currents, and supply currents. Moreover, the devices exhibit low noise and low harmonic distortion, making them ideal for use in high fidelity audio amplifier applications.

These devices are available in single, dual and quad operational amplifiers which are pin-compatible with the industry standard MC1741, MC1458, and the MC3403/LM324 bipolar products.

Low Input Noise Voltage: 18 nV/√Hz Typ
 Low Harmonic Distortion: 0.01% Typ

• Low Input Bias and Offset Currents

• High Input Impedance: $10^{12} \Omega$ Typ

• High Slew Rate: 13 V/μs Typ

Wide Gain Bandwidth: 4.0 MHz Typ

• Low Supply Current: 1.4 mA per Amp

TL071C,AC TL072C,AC TL074C,AC

LOW NOISE, JFET INPUT OPERATIONAL AMPLIFIERS

SEMICONDUCTOR TECHNICAL DATA

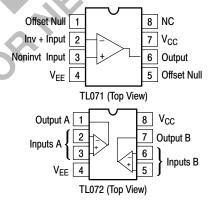






D SUFFIX
PLASTIC PACKAGE
CASE 751
(SO-8)

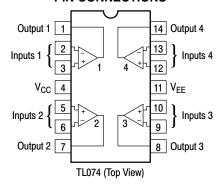
PIN CONNECTIONS





N SUFFIX PLASTIC PACKAGE CASE 646 (TL074 Only)

PIN CONNECTIONS



ORDERING INFORMATION

Op Amp Function	Device	Operating Temperature Range	Package
Cinala	TL071CD	T 00 to 1700C	SO-8
Single	TL071ACP	$T_A = 0^{\circ} \text{ to } +70^{\circ}\text{C}$	Plastic DIP
Dural	TL072CD	T 00 to .700C	SO-8
Dual	TL072ACP	$T_A = 0^{\circ} \text{ to } +70^{\circ}\text{C}$	Plastic DIP
Quad	TL074CN, ACN	$T_A = 0^\circ \text{ to } +70^\circ \text{C}$	Plastic DIP

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Supply Voltage	V _{CC} V _{EE}	18 –18	V
Differential Input Voltage	V _{ID}	±30	V
Input Voltage Range (Note 1)	V _{IDR}	±15	V
Output Short Circuit Duration (Note 2)	t _{SC}	Continuous	
Power Dissipation Plastic Package (N, P) Derate above T _A = 47°C	P _D 1.0/θ _{JA}	680 10	mW mW/°C
Operating Ambient Temperature Range	T _A	0 to +70	°C
Storage Temperature Range	T _{stg}	-65 to +150	°C

- 2. The output may be shorted to ground or either supply. Temperature and/or supply voltages must be limited to ensure that power dissipation ratings are not exceeded.
- 3. ESD data available upon request.

ELECTRICAL CHARACTERISTICS ($V_{CC} = 15 \text{ V}$, $V_{EE} = -15 \text{ V}$, $T_A = T_{high}$ to T_{low} [Note 1])

**							
Operating Ambient Temperature Range	T _A	0 to +70	°C				
Storage Temperature Range T _{stg} -65 to +150 °C							
NOTES: 1. The magnitude of the input voltage must not 15 V, whichever is less. 2. The output may be shorted to ground or eithe must be limited to ensure that power dissipating. 3. ESD data available upon request. ELECTRICAL CHARACTERISTICS (V _{CC} =	r supply. Tempe on ratings are n	erature and/or supply volt ot exceeded.	ages		OF	516	
Characteristic	s		Symbol	Min	Тур	Max	Unit
Input Offset Voltage ($R_S \le 10 \text{ k}$, $V_{CM} = 0$) TL071C, TL072C TL074C TL07_AC			V _{IO}	- - -	- - -	13 13 7.5	mV
Input Offset Current (V _{CM} = 0) (Note 2) TL07_C TL07_AC			lio	- -	- -	2.0 2.0	nA
Input Bias Current (V _{CM} = 0) (Note 2) TL07_C TL07_AC			I _{IB}	_ _	_ _	7.0 7.0	nA
Large–Signal Voltage Gain ($V_O = \pm 10 \text{ V}$, $R_L \ge 2.0 \text{ TL07_C}$ TL07_AC) k)		A _{VOL}	15 25	_ _	_ _	V/mV
Output Voltage Swing (Peak–to–Peak) $ (R_L \ge 10 \text{ k}) \\ (R_L \ge 2.0 \text{ k}) $	MIL		Vo	24 20	_ _	_ _	V

NOTES: 1. $T_{low} = 0^{\circ}C$ for TL071C,AC $T_{high} = 70$ °C for TL071C,AC TL072C,AC TL072C,AC TL074C,AC TL074C,AC

Figure 1. Unity Gain Voltage Follower

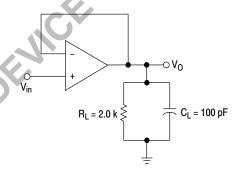
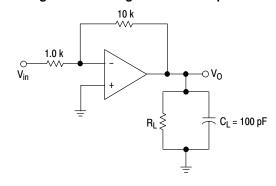


Figure 2. Inverting Gain of 10 Amplifier



^{2.} Input Bias currents of JFET input op amps approximately double for every 10°C rise in junction temperature as shown in Figure 3. To maintain junction temperature as close to ambient temperature as possible, pulse techniques must be used during testing.

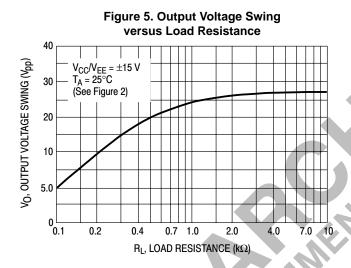
ELECTRICAL CHARACTERISTICS (V_{CC} = 15 V, V_{EE} = -15 V, T_{A} = 25°C, unless otherwise noted.)

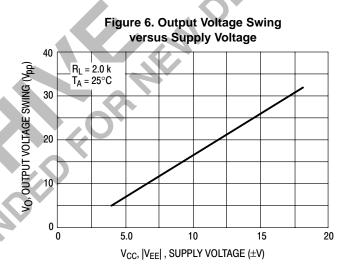
Characteristics	Symbol	Min	Тур	Max	Unit
Input Offset Voltage ($R_S \le 10 \text{ k}, V_{CM} = 0$)	V _{IO}				mV
TL071C, TL072C		_	3.0	10	
TL074C TL07_AC		_	3.0 3.0	10 6.0	
	A)/ /AT	_		0.0	\//00
Average Temperature Coefficient of Input Offset Voltage $R_S = 50 \Omega$, $T_A = T_{low}$ to T_{high} (Note 1)	$\Delta V_{IO}/\Delta T$	_	10	_	μV/°C
Input Offset Current (V _{CM =} 0) (Note 2)	I _{IO}				рА
TL07_C		_	5.0	50	
TL07_AC		_	5.0	50	
Input Bias Current (V _{CM} = 0) (Note 2) TL07_C	I _{IB}		30	200	pΑ
TL07_C		_	30	200	1
Input Resistance	r _i	_	10 ¹²	(Ω
Common Mode Input Voltage Range	V _{ICR}			(6)	V
TL07_C		±10	15, –12	_	
TL07_AC		±11	15, –12	\ -	
Large–Signal Voltage Gain ($V_0 = \pm 10 \text{ V}, R_L \ge 2.0 \text{ k}$)	A _{VOL}				V/mV
TL07_C TL07_AC		25 50	150 150	_	
		24			V
Output Voltage Swing (Peak-to-Peak) (R _L = 10 k)	Vo	24	28	_	V
Common Mode Rejection Ratio (R _S ≤ 10 k)	CMRR	0			dB
TL07_C		70	100	_	
TL07_AC		80	100	_	
Supply Voltage Rejection Ratio (R _S ≤ 10 k)	PSRR	70	100		dB
TL07_C TL07_AC		70 80	100 100	_	
Supply Current (Each Amplifier)	I _D	_	1.4	2.5	mA
Unity Gain Bandwidth	BW	_	4.0	-	MHz
Slew Rate (See Figure 1) V _{in} = 10 V, R _L = 2.0 k, C _L = 100 pF	SR	-	13	_	v/μs
Rise Time (See Figure 1)	t _r	-	0.1	-	μs
Overshoot (V _{in} = 20 mV, R _L = 2.0 k, C _L = 100 pF)	OS	_	10	-	%
Equivalent Input Noise Voltage	e _n	-	18	-	nV/√Hz
$R_S = 100 \Omega$, $f = 1000 Hz$					
Equivalent Input Noise Current $R_S = 100 \Omega$, $f = 1000 Hz$	i _n	_	0.01	_	pA/√Hz
Total Harmonic Distortion	THD	-	0.01	-	%
V_{O} (RMS) = 10 V, $R_{S} \le 1.0$ k, $R_{L} \ge 2.0$ k, f = 1000 Hz					
Channel Separation	CS	-	120	_	dB
$A_{V} = 100$					

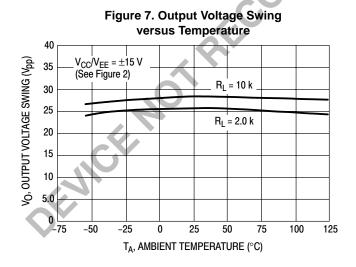
NOTES: 1. T_{low} = 0°C for TL071C,AC
T_{high} = 70°C for TL071C,AC
TL072C,AC
TL074C,AC
TL074C,AC
TL074C,AC
2. Input Bias currents of JFET input op amps approximately double for every 10°C rise in junction temperature as shown in Figure 3. To maintain junction temperature as close to ambient temperature as possible, pulse techniques must be used during testing.

Figure 3. Input Bias Current versus Temperature 100 IB, INPUT BIAS CURRENT (nA) $V_{CC}/V_{EE} = \pm 15 \text{ V}$ 1.0 0.1 0.01 -100 -75 -50 -25 0 25 50 75 100 125 150 TA, AMBIENT TEMPERATURE (°C)

Figure 4. Output Voltage Swing versus Frequency 35 $R_L = 2.0 \text{ k}$ $T_A = 25^{\circ}\text{C}$ (See Figure 2) VO, OUTPUT VOLTAGE SWING (Vpp) 30 $V_{CC}/V_{EE} = \pm 15 V$ 25 20 ±10 V 15 10 ±5.0 V 5.0 0 100 1.0 M 1.0 k 10 k 100 k 10 M f, FREQUENCY (Hz)







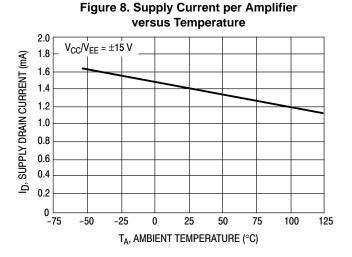
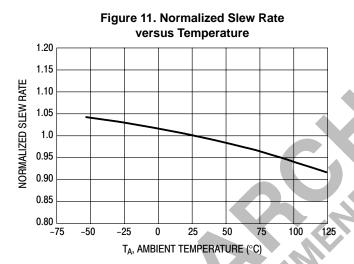
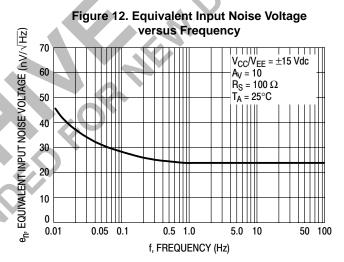
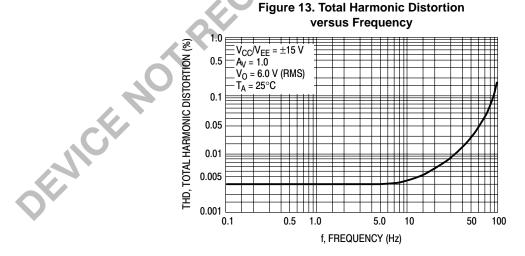


Figure 9. Large Signal Voltage Gain and **Phase Shift versus Frequency** 10⁸ $V_{CC}/V_{EE} = \pm 15 \text{ V}$ 10⁷ $R_L = 2.0 \text{ k}$ PHASE SHIFT (DEGREES) V_{VOL}, OPEN-LOOP GAIN $T_A = 25^{\circ}C$ 10⁶ 10⁵ Gain 10³ 45° 10² 90° Phase Shift 10¹ 135° 1.0 180° 10 100 1.0 k 10 k 100 k 1.0 M 10 M 100 M f, FREQUENCY (Hz)

Figure 10. Large Signal Voltage Gain versus Temperature 1000 $V_{CC}/V_{EE} = \pm 15 \text{ V}$ $V_{O} = \pm 10 \text{ V}$ $R_{L} = 2.0 \text{ k}$ V_{VOL}, VOLTAGE GAIN (V/mV) 100 10 1.0 -100 -75 -50 -25 0 25 50 75 100 TA, AMBIENT TEMPERATURE (°C)







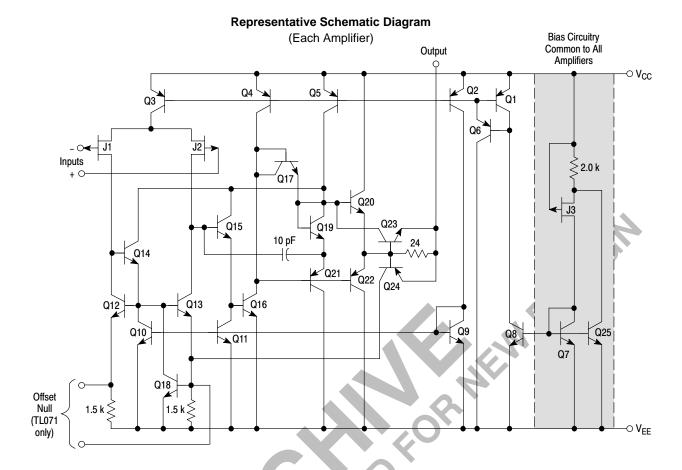


Figure 14. Audio Tone Control Amplifier

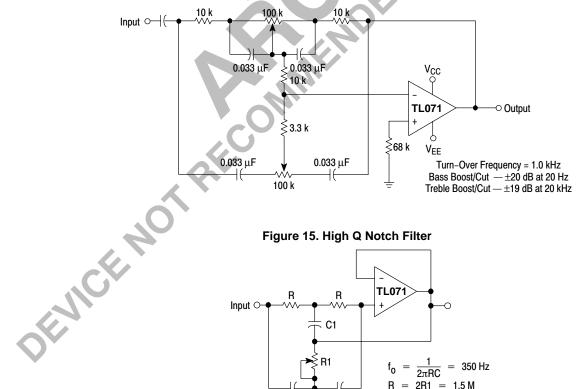
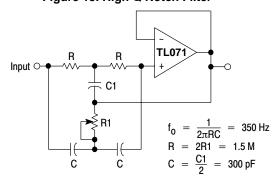
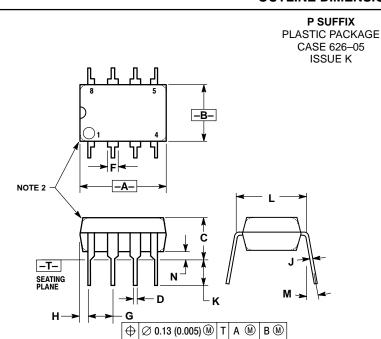


Figure 15. High Q Notch Filter



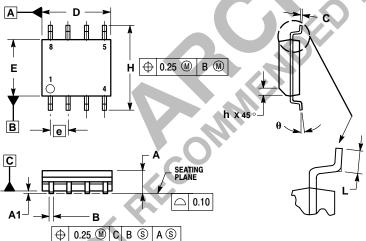
OUTLINE DIMENSIONS



- NOTES:
 1. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.
 2. PACKAGE CONTOUR OPTIONAL (ROUND OR SQUARE CORNERS).
 3. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

	MILLIN	IETERS	INCHES			
DIM	MIN	MAX	MIN	MAX		
Α	9.40	10.16	0.370	0.400		
В	6.10	6.60	0.240	0.260		
C	3.94	4.45	0.155	0.175		
D	0.38	0.51	0.015	0.020		
F	1.02	1.78	0.040	0.070		
G	2.54 BSC		0.100 BSC			
Н	0.76	1.27	0.030	0.050		
7	0.20	0.30	0.008	0.012		
K	2.92	3.43	0.115	0.135		
L	7.62 BSC		0.300 BSC			
M		10°		10°		
N	0.76	1.01	0.030	0.040		





OEVICE N

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 114-3M, 1994.

 DIMENSIONS ARE IN MILLIMETERS.

 DIMENSION D AND E DO NOT INCLUDE MOLD PROTRUSION.

 MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
- PROTRUSION B DOES NOT INCLUDE MOLD
 PROTRUSION. ALLOWABLE DAMBAR
 PROTRUSION SHALL BE 0.127 TOTAL IN EXCESS OF THE B DIMENSION AT MAXIMUM MATERIAL

	MILLIMETERS				
DIM	MIN	MAX			
Α	1.35	1.75			
A1	0.10	0.25			
В	0.35	0.49			
С	0.18	0.25			
D	4.80	5.00			
Е	3.80	4.00			
е	1.27	1.27 BSC			
Н	5.80	6.20			
h	0.25	0.50			
L	0.40	1.25			
θ	0 °	7°			

OUTLINE DIMENSIONS

N SUFFIX PLASTIC PACKAGE CASE 646-06 ISSUE M R -T-SEATING PLANE **D** 14 PL 0.13 (0.005) M

NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14 5M 1982
- CONTROLLING DIMENSION: INCH.
- 3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
- 4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.
 5. ROUNDED CORNERS OPTIONAL.

	INCHES		MILLIN	IETERS			
DIM	MIN	MIN MAX		MAX MIN		MAX	
Α	0.715	0.770	18.16	18.80			
В	0.240	0.260	6.10	6.60			
C	0.145	0.185	3.69	4.69			
D	0.015	0.021	0.38	0.53			
F	0.040	0.070	1.02	1.78			
G	0.100	BSC	2.54	BSC			
Н	0.052	0.095	1.32	2.41			
_	0.008	0.015	0.20	0.38			
K	0.115	0.135	2.92	3.43			
L	0.290	0.310	7.37	7.87			
M		10°	44-	10°			
N	0.015	0.039	0.38	1.01			

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